

21. (Twice Amended) A semiconductor device comprising:  
a gate member on a semiconductor;  
a source region in the semiconductor;  
a drain region in the semiconductor, said drain region having a  
depth shallower than said source region and not deeper than 0.1  $\mu\text{m}$ ;  
a channel region being interposed between said source and drain  
regions and being adjacent to said gate [electrode] member, said channel region  
having a length not longer than 1 $\mu\text{m}$ , and  
wherein said source and drain regions extends from a surface of  
said semiconductor to said depth not longer than a thickness of said  
semiconductor,  
wherein said source region overlaps with said gate member while  
said drain region has an edge being coincide with that of said gate member.

36. (Twice Amended) A semiconductor device according to claim 33 8  
wherein said first silicon film is a floating gate which is formed over said first  
impurity region but [while said floating gate is] not formed over said second  
impurity region.

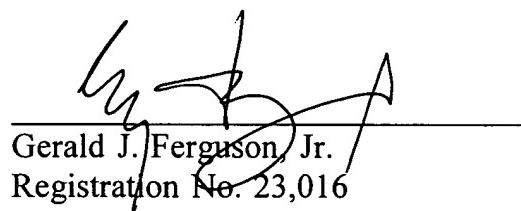
REMARKS

Reconsideration and allowance of this application are respectfully  
requested.

Referring to the rejection of claims 21-23 and 36 under 35 U.S.C. 112,  
second paragraph, claims 21 and 36 have been amended to avoid the  
informalities noted therein.

The allowance of claims 24-27, 33-35 and 37-44 is noted with appreciation.

Respectfully submitted,



Gerald J. Ferguson, Jr.  
Registration No. 23,016

Sixbey, Friedman, Leedom & Ferguson, P.C.  
8180 Greensboro Drive, Suite 800  
McLean, Virginia 22102  
(703) 790-9110